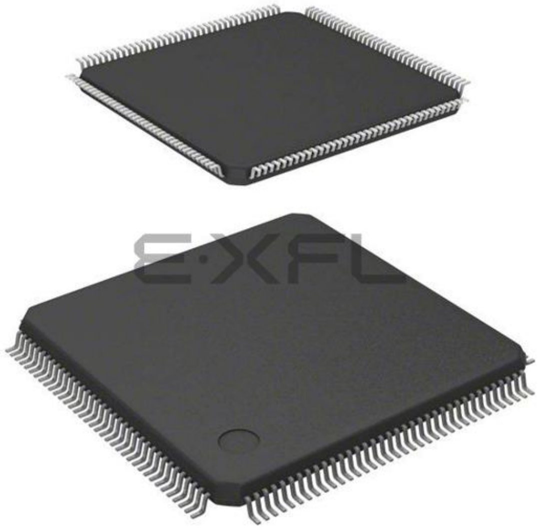

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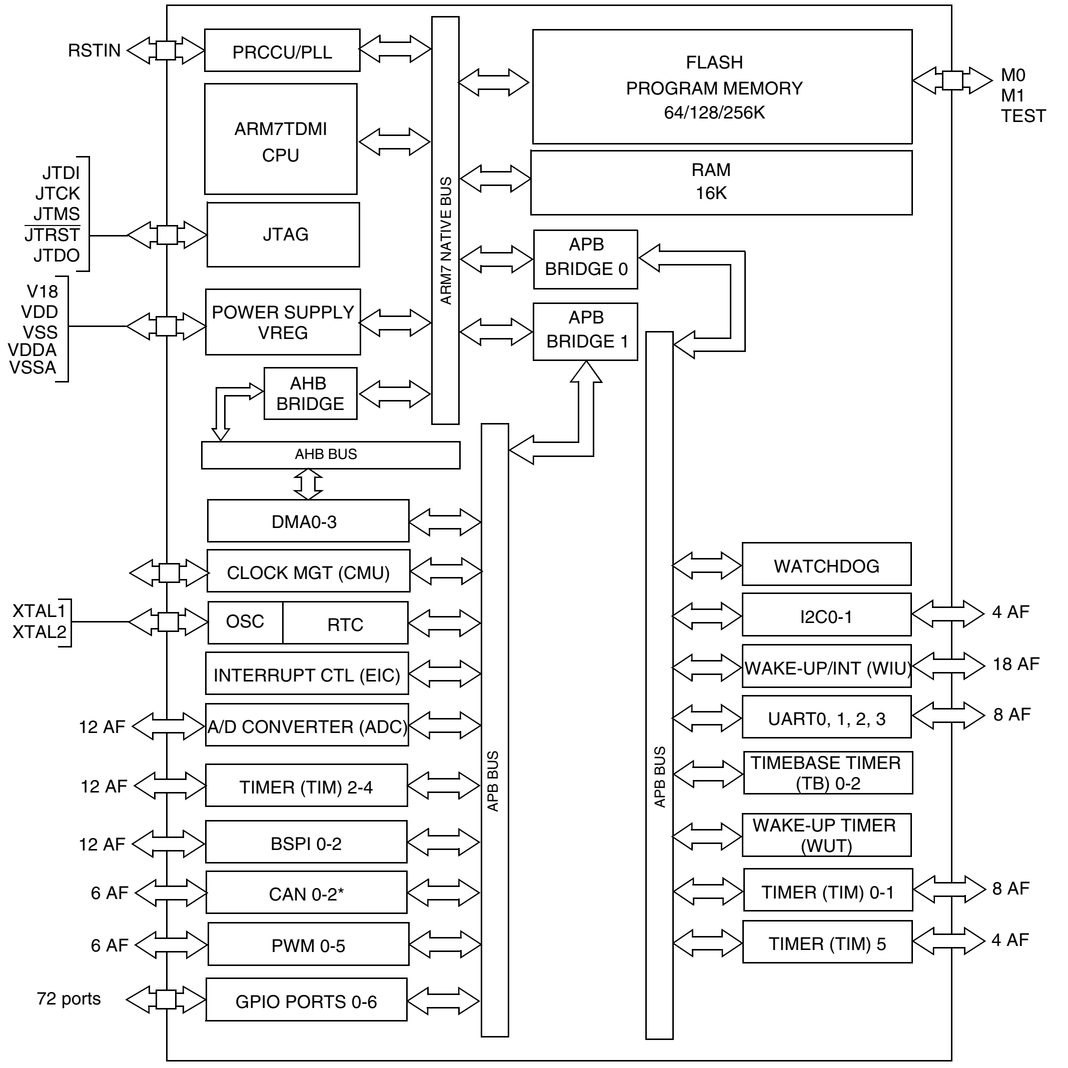
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	112
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str735fz1t6

Contents

Figure 2. STR731F/STR736 block diagram



*CAN peripherals not available on STR736F.

AF: alternate function on I/O port pin

3.1 Related documentation

Available from www.arm.com:

ARM7TDMI technical reference manual

Available from http://www.st.com:

STR73x reference manual (RM0001)

STR7 Flash programming reference manual

STR73x software library user manual

For a list of related application notes refer to http://www.st.com.

3.2.2 STR730F/STR735F (LFBGA144)

Table 3. STR730F/STR735F LFBGA ball connections

Ball	Name	Ball	Name	Ball	Name	Ball	Name
A1	P0.0 / OCMPB2	B1	P0.4 / OCMPA5	C1	P0.5 / OCMPB5	D1	V_{SS}
A2	P6.10 / WUP8	B2	P0.1 / OCMPA2	C2	P0.2 / ICAPA2	D2	V_{DD}
A3	P6.9 / TDO0	B3	P6.15 / WUP9	C3	P0.3 / ICAPB2	D3	P0.6 / ICAPA5
A4	P6.12 / MOSI0	B4	P6.13 / SCKO / WUP11	C4	P6.14 / SSO	D4	P0.7 /ICAPB5
A5	P6.6 / WUP6	B5	P6.7 / WUP7	C5	P6.8 / RDI0 / WUP10	D5	P6.11 / MISO0
A6	V_{18}	B6	P6.2 / WUP2 / RDI3	C6	P6.3 / WUP3	D6	P6.4 / WUP4 /TDO3
A7	P5.15 / INT13	B7	P5.14 / INT12	C7	V_{SS}	D7	VDD
A8	P5.8 / INT6	B8	P5.9 / INT7	C8	P5.10 / INT8 / RDI2	D8	P5.12 / INT10
A9	P5.2 / OCMPA9	B9	P5.3 / OCMPB9	C9	P5.4 / SS2	D9	P5.5 / SCK2 / WUP23
A10	P5.7 / MISO2	B10	P5.0 / MOSI1	C10	P5.1 / MISO1	D10	P4.13 / ICAPB9
A11	P5.6 / MOSI2	B11	P4.15 / SCK1 / WUP22	C11	P4.14 / SS1	D11	P4.12 / ICAPA9 / WUP21
A12	P5.11 / TDO2 / INT9	B12	P4.8 / OCMPA8	C12	P4.7 / SDA1	D12	P4.11 / OCMPB8
E1	P0.8 / OCMPA6	F1	V_{DD}	G1	V_{SS}	H1	V_{DD}
E2	P0.9 / OCMPB6	F2	P0.13 / ICAPB3	G2	P1.2 / ICAPB4	H2	P1.8 / OCMPA0 / INT0
E3	P0.10 / OCMPA7	F3	P0.14 / OCMPB3	G3	P1.3 / ICAPA4	H3	P1.9 / OCMPB0 / INT1
E4	P0.11 / OCMPB7	F4	P0.15 / OCMPA3	G4	V_{SS}	H4	P1.10 / ICAPB0 / WUP28
E5	P0.12 / ICAPA3	F5	P1.0 / OCMPA4	G5	P1.5	H5	XTAL2
E6	P6.5 / WUP5	F6	P1.1 / OCMPB4	G6	P2.11 / WUP17	H6	P2.10 / WUP16
E7	P6.0 / WUP0	F7	P6.1 / WUP1	G7	P4.0 / ICAPA7 / WUP24	H7	P2.15 / SDA 0
E8	P5.13 / INT11	F8	P4.4 / CAN2TX[1)]	G8	VDD	H8	JTMS
E9	P4.10 / ICAPA6 / WUP20	F9	P4.3 / ICAPB8 / WUP27	G9	VSS	H9	VSS
E10	P4.9 / ICAPB6	F10	P4.2 / ICAPA8 / WUP26	G10	JTDO	H10	VDD
E11	P4.6 / SCL1 / WUP19	F11	P4.1 / ICAPB7 / WUP25	G11	JTCK	H11	P3.15 / AIN15 / INT5
E12	P4.5 / WUP18 / CAN2RX[1)]	F12	JTDI	G12	nJTRST	H12	P3.14 / AIN14 / INT4
J1	P1.4	K1	P1.6 / OCMPB1	L1	P1.7 / OCMPA1	M1	P1.14 / CAN0RX[1)] / WUP12
J2	P1.11 / ICAPA0 / WUP29	K2	P1.13 / ICAPB1 / WUP31	L2	P1.15 / CAN0TX[1)]	M2	P2.4 / PWM2
J3	P1.12 / ICAPA1 / WUP30	K3	P2.1 / CAN1RX[1)] / WUP13	L3	P2.0 / PWM0	M3	P2.5 / PWM3
J4	P2.7 / PWM5	K4	P2.6 / PWM4	L4	P2.3 / PWM1	M4	P2.2 / CAN1TX[1)]
J5	V_{DD}	K5	M1	L5	RSTIN	M5	M0
J6	P2.9 / RDI1 / WUP14	K6	P2.8 / TDO1	L6	V_{SS}	M6	V_{SS}
J7	P2.14 / SCL 0 / WUP15	K7	P2.13 / INT15	L7	P2.12 / INT14	M7	XTAL1
J8	P3.1 / AIN1	K8	P3.0 / AIN0	L8	VBIAS	M8	TST
J9	P3.13 / AIN13 / INT3	K9	P3.4 / AIN4	L9	P3.3 / AIN3	M9	P3.2 / AIN2
J10	P3.12 / AIN12 / INT2	K10	V_{DDA}	L10	P3.5 / AIN5	M10	V_{SS}
J11	P3.9 / AIN9	K11	V_{SSA}	L11	P3.7 / AIN7	M11	V_{DD}
J12	P3.8 / AIN8	K12	P3.11 / AIN11	L12	P3.10 / AIN10	M12	P3.6 / AIN6

Note: CAN alternate functions not available on STR735F.

Legend / Abbreviations for Table 4:

Type: I = input, O = output, S = supply, HiZ= high impedance,

In/Output level: T_T= TTL 0.8 V / 2 V with input trigger
C_T= CMOS $0.3V_{DD}/0.7V_{DD}$ with input trigger

Port and control configuration:

Input: pu/pd = with internal 100 kΩ weak pull-up or pull down

Output: OD = open drain (logic level)
PP = push-pull

Interrupts:

INTx = external interrupt line

WUPx = wake-up interrupt line

The reset state (during and just after the reset) of the I/O ports is input floating (Input tristate TTL mode). To avoid excess power consumption, unused I/O ports must be tied to ground.

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP		
1	A1	1	P0.0/OCMPB2	I/O	T_T			2mA	X	X	Port 0.0	TIM2: output compare B output
2	B2	2	P0.1/OCMPA2	I/O	T_T			2mA	X	X	Port 0.1	TIM2: output compare A output
3	C2	3	P0.2/ICAPA2	I/O	T_T			2mA	X	X	Port 0.2	TIM2: input capture A input
4	C3	4	P0.3/ICAPB2	I/O	T_T			2mA	X	X	Port 0.3	TIM2: input capture B input
5	D1		V_{SS}	S							Ground	
6	D2		V_{DD}	S							Supply voltage (5 V)	
7	B1	5	P0.4/OCMPA5	I/O	T_T			2mA	X	X	Port 0.4	TIM5: output compare A output
8	C1	6	P0.5/OCMPB5	I/O	T_T			2mA	X	X	Port 0.5	TIM5: output compare B output
9	D3	7	P0.6/ICAPA5	I/O	T_T			2mA	X	X	Port 0.6	TIM5: input capture A input
10	D4		P0.7/ICAPB5	I/O	T_T			2mA	X	X	Port 0.7	TIM5: input capture B input
11	E1		P0.8/OCMPA6	I/O	T_T			2mA	X	X	Port 0.8	TIM6: output compare A output
12	E2		P0.9/OCMPB6	I/O	T_T			2mA	X	X	Port 0.9	TIM6: output compare B output
13	E3		P0.10/OCMPA7	I/O	T_T			2mA	X	X	Port 0.10	TIM7: output compare A output
14	E4		P0.11/OCMPB7	I/O	T_T			2mA	X	X	Port 0.11	TIM7: output compare B output
15	F1	8	V_{DD}	S							Supply voltage (5 V)	
16	G1	9	V_{SS}	S							Ground	
17	E5	10	P0.12/ICAPA3	I/O	T_T			2mA	X	X	Port 0.12	TIM3: input capture A input
18	F2	11	P0.13/ICAPB3	I/O	T_T			2mA	X	X	Port 0.13	TIM3: input capture B input

Table 4. STR73xF pin description

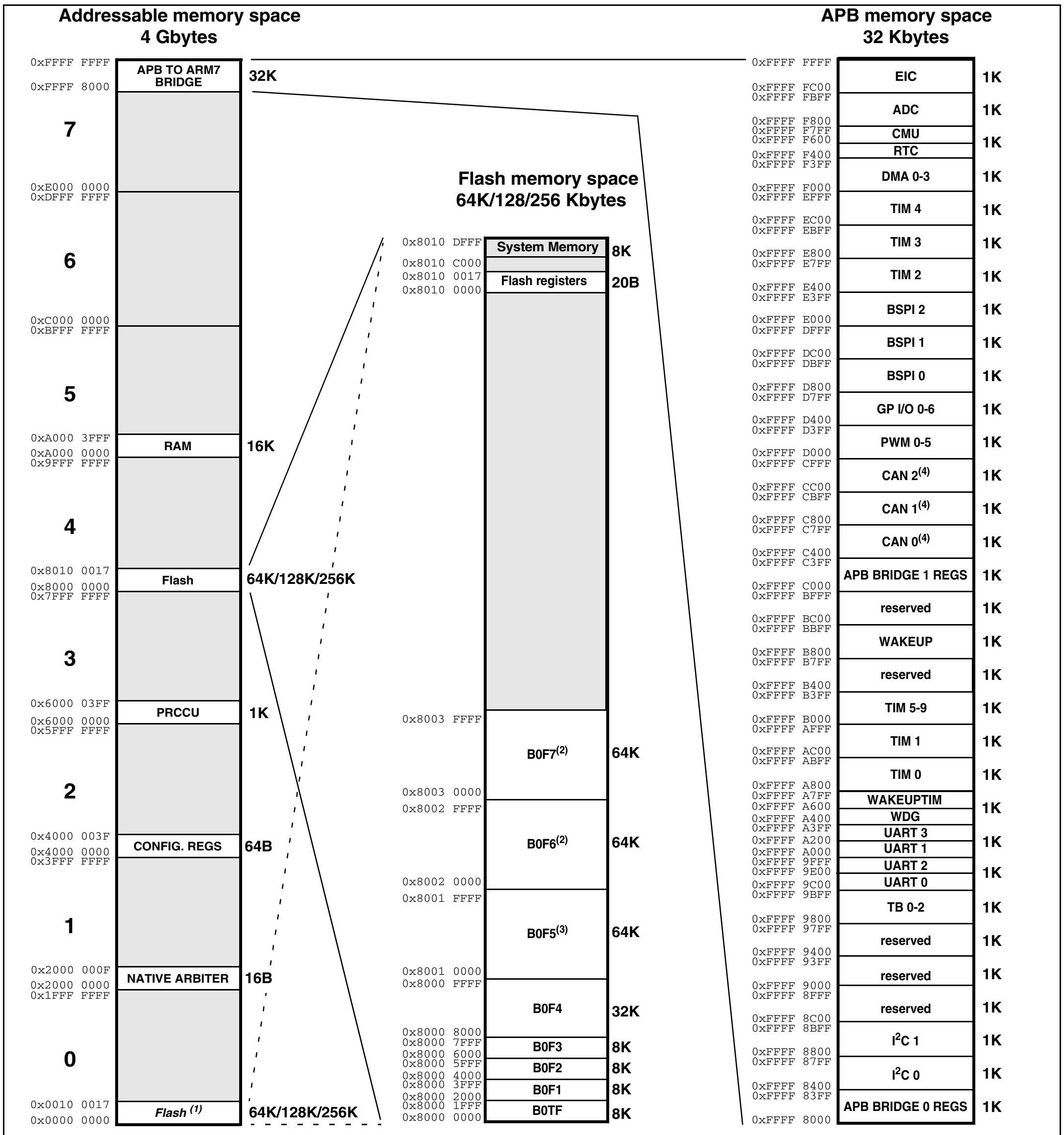
Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function	
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP			
50	J5	36	V_{DD}	S							Supply voltage (5 V)		
51	M6	37	V_{SS}	S							Ground		
52	M7	38	XTAL1	I							Oscillator amplifier circuit input and internal clock generator input.		
53	H5	39	XTAL2	O							Oscillator amplifier circuit output.		
54	L6	40	V_{SS}	S							Ground		
55	K6	41	P2.8/TDO1/CAN2RX	I/O	T_T			2mA	X	X	Port 2.8	UART1: transmit data output	CAN2: receive data input (TQFP100 only)
56	J6	42	P2.9/RDI1/CAN2TX	I/O	T_T		WUP14	2mA	X	X	Port 2.9	UART1: receive data input	CAN2: transmit data output (TQFP100 only)
57	H6		P2.10	I/O	T_T		WUP16	2mA	X	X	Port 2.10		
58	G6		P2.11	I/O	T_T		WUP17	2mA	X	X	Port 2.11		
59	L7		P2.12	I/O	T_T		INT14	2mA	X	X	Port 2.12		
60	K7		P2.13	I/O	T_T		INT15	2mA	X	X	Port 2.13		
61	J7	43	P2.14/SCL0	I/O	T_T		WUP15	2mA	X	X	Port 2.14	I2C0: serial clock	
62	H7	44	P2.15/SDA0	I/O	T_T			2mA	X	X	Port 2.15	I2C0: serial data	
63	M8	45	Test	I		pd					Reserved pin. Must be tied to ground		
64	L8	46	V_{BIAS}	S							Internal RC oscillator bias. A 1.3 MΩ external resistor has to be connected to this pin when a 32 kHZ RC oscillator frequency is used.		
65	M10	47	V_{SS}	S							Ground		
66	M11	48	V_{DD}	S							Supply voltage (5 V)		
67	K8		P3.0/AIN0	I/O	T_T			2mA	X	X	Port 3.0	ADC: analog input 0	
68	J8		P3.1/AIN1	I/O	T_T			2mA	X	X	Port 3.1	ADC: analog input 1	
69	M9		P3.2/AIN2	I/O	T_T			2mA	X	X	Port 3.2	ADC: analog input 2	
70	L9		P3.3/AIN3	I/O	T_T			2mA	X	X	Port 3.3	ADC: analog input 3	
71	K9	49	P3.4/AIN4	I/O	T_T			2mA	X	X	Port 3.4	ADC: analog input 4 (AIN0 in TQFP100)	
72	L10	50	P3.5/AIN5	I/O	T_T			2mA	X	X	Port 3.5	ADC: Analog input 5 (AIN1 in TQFP100)	

3.3 Memory mapping

Figure 5 shows the various memory configurations of the STR73xF system. The system memory map (from 0x0000_0000 to 0xFFFF_FFFF) is shown on the left part of the figure, the right part shows maps of the Flash and APB areas. For flexibility the Flash or RAM addresses can be aliased to Block 0 addresses using the remapping feature

Most reserved memory spaces (gray shaded areas in *Figure 5*) are protected from access by the user code. When an access this memory space is attempted, an ABORT signal is generated. Depending on the type of access, the ARM processor will enter “prefetch abort” state (Exception vector 0x0000_000C) or “data abort” state (Exception vector 0x0000_0010). It is up to the application software to manage these abort exceptions.

Figure 5. Memory map



(1) Flash aliased at 0x0000 0000h by system decoder for booting with valid instruction upon RESET from Block B0 (8 Kbytes)

(2) Only available in STR73xZ2/V2

(3) Only available in STR73xZ2/V2 and STR73xZ1/V1

(4) Only available in STR730/STR731

access to gray shaded area will return an ABORT

Drawing not to scale

4.2 Absolute maximum ratings

Stresses above those listed as “absolute maximum ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 5. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V_{DD} - V_{SS}	External 5 V Supply voltage	-0.3	6.0	V
V_{SSA}	Reference ground for A/D converter	V_{SS}	V_{SS}	V
V_{DDA}- V_{SSA}	Reference voltage for A/D converter	-0.3	V_{DD}+0.3	V
V_{IN}	Input voltage on any pin	-0.3	V_{DD}+0.3	V
$\lvert\Delta V_{DDx}\rvert$	Variations between different 5 V power pins	-	0.3	mV
$\lvert V_{SSX}$ - $V_{SS}\rvert$	Variations between all the different ground pins	-	0.3	mV
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	see *: Absolute maximum ratings (electrical sensitivity) on page 36*		
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)			

Table 6. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD} power lines (source) [1]	100	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink) [1]	100	mA
I_{IO}	Output current sunk by any I/O and control pin	10	mA
	Output current source by any I/O and control pin	10	mA
$I_{INJ(PIN)}$ [2) & 3)]	Injected current on any other pin [4) &5)]	±10	mA
$\Sigma I_{INJ(PIN)}$ [2]	Total injected current (sum of all I/O and control pins) [4]	±75	mA

1. All 5 V power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external 5 V supply
2. $I_{INJ(PIN)}$ must never be exceeded. This is implicitly insured if V_{IN} maximum is respected. If V_{IN} maximum cannot be respected, the injection current must be limited externally to the $I_{INJ(PIN)}$ value. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$.
3. Negative injection disturbs the analog performance of the device. See note in *Section 4.3.6: 10-bit ADC characteristics on page 43*.
4. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values). These results are based on characterization with $\Sigma I_{INJ(PIN)}$ maximum current injection on four I/O port pins of the device.

5.) In 144-pin devices, only +10 mA on P0.3, P1.13, P3.6 and P4.13 pins (negative injection not allowed).

Table 7. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-55 to +150	°C
T_J	Maximum junction temperature (see *Section 5.2: Thermal characteristics on page 48*)		

4.3.1 Supply current characteristics

The current consumption is measured as described in *Figure 6* and *Figure 7*.

Total current consumption

The MCU is placed under the following conditions:

- All I/O pins in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except if explicitly mentioned.

Subject to general operating conditions for V_{DD}, and T_A.

Table 10. Total current consumption

Symbol	Parameter	Conditions	Typ [1]	Max [2]	Unit
I_{DD}	RUN mode[3]	Formula, f_{MCLK} in MHz, RAM execution	7 + 1.9 f_{MCLK}		mA
		f_{MCLK} = 36 MHz, RAM execution	76		mA
		f_{MCLK} = 36 MHz, Flash execution	86		mA
	WFI mode	f_{OSC} = 4 MHz, f_{MCLK}= f_{OSC}/16 = 250 kHz Main voltage regulator ON, LP voltage regulator = 2 mA, RTC and WDG on, other modules off.	6.7	8	mA
	LPWFI mode	f_{RC} = high frequency (CMU_RCCTL= 0x8), f_{MCLK}= f_{RC} /16, LP voltage regulator = 2 mA, other modules off.	220	350	µA
	STOP mode	f_{OSC} = 4 MHz, RC oscillator on f_{RC} = high frequency (CMU_RCCTL= 0x0) LP voltage regulator = 6 mA, RTC and WUT ON, other modules off. Internal wake-up possible.	500	700	µA
		f_{RC} = high frequency (CMU_RCCTL= 0xF), LP voltage regulator = 2mA. WUT ON, other modules off. Internal wake-up possible.	150	220	
		LP voltage regulator = 2 mA, WIU on, Other modules off, external wake-up.	50	140	
	HALT mode	LP voltage regulator = 2 mA.	50	140	µA

1. Typical data are based on T_A=25° C, V_{DD}=5 V
2. Data based on characterization results, tested in production at V_{DD} max. and T_A = 25° C.
3. I/O in static configuration (not toggling). RUN mode is almost **independent of temperature**. On the contrary RUN mode current is **highly dependent on the application**. The I_{DDRUN} value can be significantly reduced by the application in the following ways: switch-off unused peripherals (default), reduce peripheral frequency through internal prescaler, fetch the most frequently-used functions from RAM and use low power mode when possible.

Main oscillator characteristics

V_{DD} = 5 V ± 10%, T_A = -40° C to T_{Amax}, unless otherwise specified.

Table 14. Main oscillator characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{OSC}	Oscillator frequency		4		8	MHz
g_m	Oscillator transconductance		1.5		4.2	mA/V
V_{OSC} 1)	Oscillation amplitude	f_{OSC} = 4 MHz, T_A= 25° C	-	2.4	-	V
		f_{OSC} = 8 MHz, T_A= 25° C		1.-		
V_{AV} 1)	Oscillator operating point	Sine wave middle, T_A= 25° C	-	0.77	-	V
t_{STUP} 1)	Oscillator start-up time	External crystal, V_{DD} = 5.5 V, f_{OSC} = 4 MHz, T_A=-40° C	-	-	12	ms
		External crystal, V_{DD} = 5.0 V, f_{OSC} = 4 MHz, T_A=25° C	-	5.5	-	ms
		External crystal, V_{DD} = 5.5 V, f_{OSC} = 6 MHz, T_A=-40° C	-	-	8	ms
		External crystal, V_{DD} = 5.0 V, f_{OSC} = 6 MHz, T_A=25° C	-	3.3	-	ms
		External crystal, V_{DD} = 5.5 V, f_{OSC} = 8 MHz, T_A=-40° C	-	-	7	ms
		External crystal, V_{DD} = 5.0 V, f_{OSC} = 8 MHz, T_A= 25° C	-	2.7	-	ms

Table 14. Main oscillator characteristics (continued)

Symbol	Parameter	Conditions		Value			Unit
				Min	Typ	Max	
R_F[1]	Feedback resistor	f_{OSC} = 4 MHz Cp[2] = 10 pF	C_1[3] = C_2[4] = 10 pF	150	555	-	Ω
			$C_1 = C_2$ = 20 pF	490	1035	-	
			$C_1 = C_2$ = 30 pF	490	1030	-	
			$C_1 = C_2$ = 40 pF	380	850	-	
		f_{OSC} = 5 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	160	470	-	
			$C_1 = C_2$ = 20 pF	415	800	-	
			$C_1 = C_2$ = 30 pF	340	735	-	
			$C_1 = C_2$ = 40 pF	260	580	-	
		f_{OSC} = 6 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	160	415	-	
			$C_1 = C_2$ = 20 pF	325	640	-	
			$C_1 = C_2$ = 30 pF	250	550	-	
			$C_1 = C_2$ = 40 pF	180	420	-	
		f_{OSC} = 7 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	160	375	-	
			$C_1 = C_2$ = 20 pF	260	525	-	
			$C_1 = C_2$ = 30 pF	185	420	-	
			$C_1 = C_2$ = 40 pF	135	315	-	
		f_{OSC} = 8 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	155	340	-	
			$C_1 = C_2$ = 20 pF	210	435	-	
			$C_1 = C_2$ = 30 pF	145	335	-	
			$C_1 = C_2$ = 40 pF	100	245	-	

1. Min and max values are guaranteed by characterization, not tested in production.
2. C_P represents the total capacitance between XTAL1 and XTAL2, including the shunt capacitance of the external quartz crystal as well as the total board parasitic cross-capacitance between XTAL1 track and XTAL2 track.
3. C_1 represents the total capacitance between XTAL1 and ground, including the external capacitance tied to XTAL1 pin (C_L) as well as the total parasitic capacitance between XTAL1 track and ground (this includes application board track capacitance to ground and device pin capacitance).
4. C_2 represents the total capacitance between XTAL2 and ground, including the external capacitance tied to XTAL1 pin (C_L) as well as the total parasitic capacitance between XTAL2 track and ground (this includes application board track capacitance to ground and device pin capacitance).

Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm SAE J 1752/3 which specifies the board and the loading of each pin.

Table 20. EMI data

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. $[f_{OSC4M}/f_{MCLK}]$ 6/36 MHz	Max vs. $[f_{OSC4M}/f_{MCLK}]$ 8/8 MHz	Unit
S_{EMI}	Peak level	V_{DD}=5.0V, T_A=+25°C, All packages	0.1 MHz to 30 MHz	23	30	dBµV
			30 MHz to 130 MHz	37	34	
			130 MHz to 1 GHz	20	7	
			SAE EMI Level	4	3.5	-

Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU and DLU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). Two models can be simulated: human body model and machine model. This test conforms to the JESD22-A114A/A115A standard.

Table 21. ESD Absolute Maximum ratings

Symbol	Ratings	Conditions	Maximum value [1)]	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A=+25° C	2000	V
$V_{ESD(MM)}$	Electrostatic discharge voltage (machine model)		200	
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)		750 on corner pins, 500 on others	

Notes:

1. Data based on characterization results, not tested in production.

Static and dynamic latch-up

- **LU**: 3 complementary static tests are required on 10 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

- **DLU**: Electrostatic discharges (one positive then one negative test) are applied to each pin of 3 samples when the micro is running to assess the latch-up performance in dynamic mode. Power supplies are set to the typical values, the oscillator is connected as near as possible to the pins of the micro and the component is put in reset mode. This test conforms to the IEC1000-4-2 and SAEJ1752/3 standards. For more details, refer to the application note AN1181.

Table 22. Electrical sensitivities

Symbol	Parameter	Conditions	Class [1)]
LU	Static latch-up class	T_A=+25°C T_A=+85°C T_A=+105°C	A A A
DLU	Dynamic latch-up class	V_{DD}= 5.5 V, f_{OSC4M} = 4 MHz, f_{MCLK} = 32 MHz, T_A = +25° C	A

1. Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to Class A it exceeds the JEDEC standard. B Class strictly covers all the JEDEC criteria (international standard).

4.3.5 I/O port pin characteristics

General characteristics

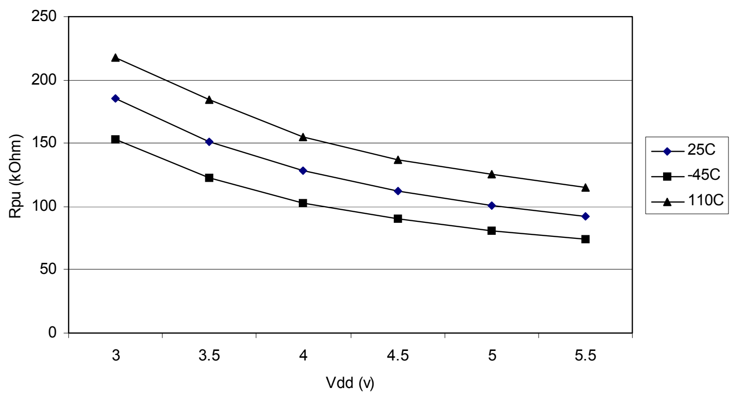
Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 23. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage [1]	TTL ports			0.8	V
V_{IH}	Input high level voltage [1]		2.0			
$I_{INJ(PIN)}$	Injected current on any I/O pin				±10	mA
$\Sigma I_{INJ(PIN)}$ [2]	Total injected current (sum of all I/O and control pins)				±75	mA
I_{lkg}	Input leakage current [3]	$V_{SS} \leq V_{IN} \leq V_{DD}$			±1	µA
I_S	Static current consumption [4]	Floating input mode		200		µA
R_{PU}	Weak pull-up equivalent resistor[5]	$V_{IN}=V_{SS}$	55	120	220	kΩ
R_{PD}	Weak pull-down equivalent resistor[5]	$V_{IN}=V_{DD}$	55	120	220	kΩ
C_{IO}	I/O pin capacitance			5		pF

1. Data based on characterization results, not tested in production.
2. When the current limitation is not possible, the V_{IN} absolute maximum rating must be respected, otherwise refer to $I_{INJ(PIN)}$ specification. A positive injection is induced by $V_{IN}>V_{33}$ while a negative injection is induced by $V_{IN}<V_{SS}$. Refer to *Section 4.2 on page 22* for more details.
3. Leakage could be higher than max. if negative current is injected on adjacent pins.
4. Configuration not recommended, all unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor. Data based on design simulation and/or technology characteristics, not tested in production.
6. The R_{PU} pull-up and R_{PD} pull-down equivalent resistor are based on a resistive transistor (corresponding I_{PU} and I_{PD} current characteristics described in *Figure 19*).

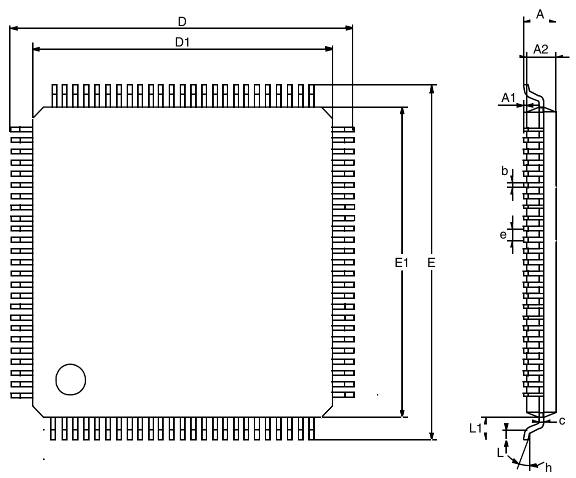
Figure 20. NRSTIN R_{PU} vs. V_{DD}



5 Package characteristics

5.1 Package mechanical data

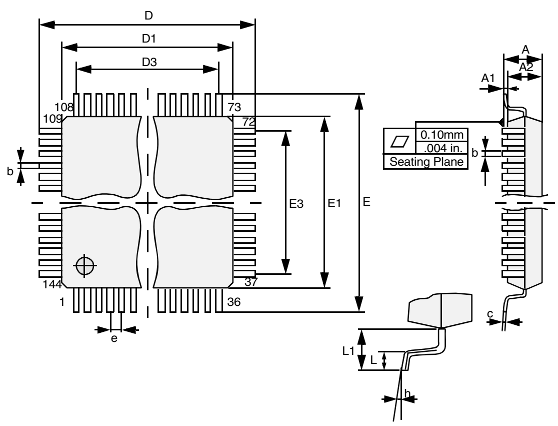
Figure 24. 100-pin thin quad flat package



Dim.	mm			inches[(1)]		
	Min	Typ	Max	Min	Typ	Max
A			1.60			0.0630
A1	0.05		0.15	0.0020		0.0059
A2	1.35	1.40	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106
C	0.09		0.20	0.0035		0.0079
D		16.00			0.6299	
D1		14.00			0.5512	
E		16.00			0.6299	
E1		14.00			0.5512	
e		0.50			0.0197	
h	0°	3.5°	7°	0°	3.5°	7°
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1		1.00			0.0394	
	Number of Pins					
N	100					

1. Values in inches are converted from mm and rounded to 4 decimal digits.

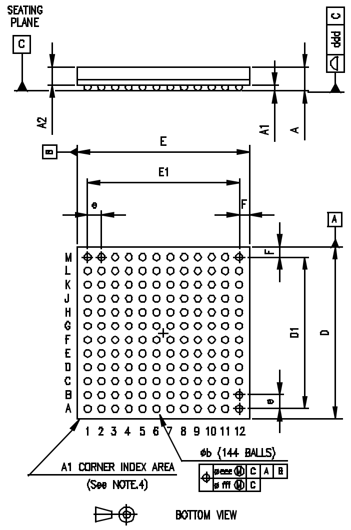
Figure 25. 144-pin thin quad flat package



Dim.	mm			inches[(1)]		
	Min	Typ	Max	Min	Typ	Max
A			1.60			0.0630
A1	0.05		0.15	0.0020		0.0059
A2	1.35	1.40	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106
c	0.09		0.20	0.0035		0.0079
D	21.80	22.00	22.20	0.8583	0.8661	0.8740
D1	19.80	20.00	20.20	0.7795	0.7874	0.7953
D3		17.50			0.6890	
E	21.80	22.00	22.20	0.8583	0.8661	0.8740
E1	19.80	20.00	20.20	0.7795	0.7874	0.7953
E3		17.50			0.6890	
e		0.50			0.0197	
K	0°	3.5°	7°	0°	3.5°	7°
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1		1.00			0.0394	
	Number of Pins					
N	144					

1. Values in inches are converted from mm and rounded to 4 decimal digits.

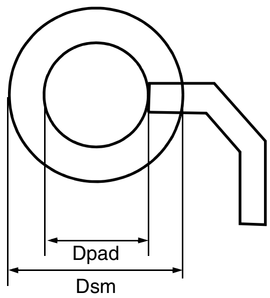
Figure 26. 144-ball low profile fine pitch ball grid array package



Dim.	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	1.21		1.70	0.0476		0.0669
A1	0.21			0.0083		
A2		1.085			0.0427	
b	0.35	0.40	0.45	0.0138	0.0157	0.0177
D	9.85	10.00	10.15	0.3878	0.3937	0.3996
D1		8.80			0.3465	
E	9.85	10.00	10.15	0.3878	0.3937	0.3996
E1		8.80			0.3465	
e		0.80			0.0315	
F		0.60			0.0236	
ddd			0.10			0.0039
eee			0.15			0.0059
fff			0.08			0.0031
	Number of Pins					
N	144					

[1]Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 27. Recommended PCB design rules (0.80/0.75mm pitch BGA)



Dpad	0.37 mm
Dsm	0.52 mm typ. (depends on solder mask registration tolerance
Solder paste	0.37 mm aperture diameter
– Non solder mask defined pads are recommended – 4 to 6 mils screen print	

5.2 Thermal characteristics

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using the following equation:

$$T_J = T_A + (P_D \times \Theta_{JA}) \qquad (1)$$

Where:

– T_A is the ambient temperature in °C,

– Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,

– P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$),

– P_{INT} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the chip internal power,

– $P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant if the device is configured to drive continuously external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273°C) \qquad (2)$$

Therefore (solving equations 1 and 2):

$$K = P_D \times (T_A + 273°C) + \Theta_{JA} \times P_D^2 \qquad (3)$$

Where:

– K is a constant for the particular part, which may be determined from equation (3) by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations (1) and (2) iteratively for any value of T_A

Table 28. Thermal characteristics

Symbol	Description	Package	Value (typical)	Unit
Θ_{JA}	Thermal resistance junction-ambient	LFBGA144	50	°C/W
		TQFP144	40	
		TQFP100	40	

8 Revision history

Table 30. Document revision history

Date	Revision	Description of changes
19-Sep-2005	1	First release
02-Nov-2005	2	Removed Table 8 power consumption in LP modes Updated PLL frequency in *Section 1.1* and *Table 12*
08-Mar-2006	3	*Section 3.4: Preliminary power consumption data* updated *Section 3.5: DC electrical characteristics* updated *Section 7: Known limitations* added
04-Jun-2006	4	*Section 4: Electrical parameters* updated *Section 7: Known limitations* updated Added temperature range -40°C to 85°C in *Section 6: Order codes*
19-Jun-2006	5	Changed Flash data retention to 20 years at 85°C in *Table 18 on page 34*.
08-Sep-2006	6	Changed *Table 24: Output driving current on page 39* Added *Figure 14: VOL standard ports vs IOL @ VDD 5 V* thru *Figure 18: VOL P6.0 pin vs IOL @ VDD 5 V on page 40*. Added *Figure 20: NRSTIN RPU vs. VDD*
08-Jun-2008	7	Inch values rounded to 4 decimal digits in *Section 5.1: Package mechanical data* Modified BSPI speed in *Section 2.1: On-chip peripherals*